

Dual/Quad Low Noise Operational Amplifiers

The MC33078/9 series is a family of high quality monolithic amplifiers employing Bipolar technology with innovative high performance concepts for quality audio and data signal processing applications. This family incorporates the use of high frequency PNP input transistors to produce amplifiers exhibiting low input voltage noise with high gain bandwidth product and slew rate. The all NPN output stage exhibits no deadband crossover distortion, large output voltage swing, excellent phase and gain margins, low open loop high frequency output impedance and symmetrical source and sink AC frequency performance.

The MC33078/9 family offers both dual and quad amplifier versions, tested over the automotive temperature range and available in the plastic DIP and SOIC packages (P and D suffixes).

• Dual Supply Operation: ±5.0 V to ±18 V

Low Voltage Noise: 4.5 nV/√Hz
Low Input Offset Voltage: 0.15 mV

Low T.C. of Input Offset Voltage: 2.0 μV/°C
 Low Total Harmonic Distortion: 0.002%

High Gain Bandwidth Product: 16 MHz

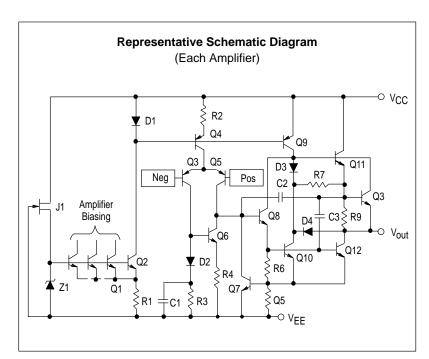
• High Slew Rate: 7.0 V/us

• High Open Loop AC Gain: 800 @ 20 kHz

• Excellent Frequency Stability

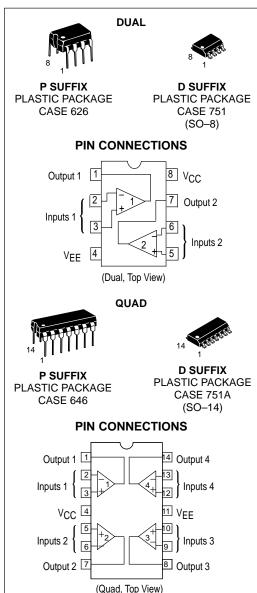
• Large Output Voltage Swing: +14.1 V/ -14.6 V

ESD Diodes Provided on the Inputs



MC33078 MC33079

DUAL/QUAD LOW NOISE OPERATIONAL AMPLIFIERS



ORDERING INFORMATION

Device	Operating Temperature Range	Package
MC33078D		SO-8
MC33078P	$T_{\Delta} = -40^{\circ} \text{ to } +85^{\circ}\text{C}$	Plastic DIP
MC33079D	1A = -40 10 +03 C	SO-14
MC33079P		Plastic DIP

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage (V _{CC} to V _{EE)}	VS	+36	V
Input Differential Voltage Range	V _{IDR}	(Note 1)	V
Input Voltage Range	V _{IR}	(Note 1)	V
Output Short Circuit Duration (Note 2)	tsc	Indefinite	sec
Maximum Junction Temperature	TJ	+150	°C
Storage Temperature	T _{stg}	-60 to +150	°C
Maximum Power Dissipation	PD	(Note 2)	mW

NOTES: 1. Either or both input voltages must not exceed the magnitude of V_{CC} or V_{EE}.

2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (see Figure 1).

DC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R _S = 10 Ω , V _{CM} = 0 V, V _O = 0 V) (MC33078) T _A = +25°C T _A = -40° to +85°C (MC33079) T _A = +25°C T _A = -40° to +85°C	IVIOI	_ _ _ _	0.15 — 0.15 —	2.0 3.0 2.5 3.5	mV
Average Temperature Coefficient of Input Offset Voltage RS = 10 Ω , V _{CM} = 0 V, V _O = 0 V, T _A = T _{low} to T _{high}	ΔV _{ΙΟ} /ΔΤ	_	2.0	_	μV/°C
Input Bias Current ($V_{CM} = 0 \text{ V}, V_{O} = 0 \text{ V}$) $T_{A} = +25^{\circ}\text{C}$ $T_{A} = -40^{\circ} \text{ to } +85^{\circ}\text{C}$	I _{IB}	_	300 —	750 800	nA
Input Offset Current ($V_{CM} = 0 \text{ V}, V_O = 0 \text{ V}$) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$	I _{IO}		25 —	150 175	nA
Common Mode Input Voltage Range ($\Delta V_{IO} = 5.0 \text{ mV}, V_{O} = 0 \text{ V}$)	VICR	±13	±14	_	V
Large Signal Voltage Gain ($V_O = \pm 10$ V, $R_L = 2.0$ k Ω) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$	AVOL	90 85	110 —	_	dB
Output Voltage Swing (V_{ID} = $\pm 1.0V$) RL = $600~\Omega$ RL = $600~\Omega$ RL = $2.0~k\Omega$ RL = $2.0~k\Omega$ RL = $10~k\Omega$ RL = $10~k\Omega$ RL = $10~k\Omega$	Vo+ Vo- Vo+ Vo- Vo+ Vo-	 +13.2 +13.5	+10.7 -11.9 +13.8 -13.7 +14.1 -14.6	 _13.2 _14	V
Common Mode Rejection ($V_{in} = \pm 13V$)	CMR	80	100	_	dB
Power Supply Rejection (Note 3) VCC/VEE = +15 V/ -15 V to +5.0 V/ -5.0 V	PSR	80	105	_	dB
Output Short Circuit Current (V _{ID} = 1.0 V, Output to Ground) Source Sink	ISC	+15 -20	+29 -37	_ _	mA
Power Supply Current ($V_O = 0$ V, All Amplifiers) (MC33078) $T_A = +25^{\circ}C$ $T_A = -40^{\circ}$ to $+85^{\circ}C$ (MC33079) $T_A = +25^{\circ}C$ $T_A = -40^{\circ}$ to $+85^{\circ}C$	ΙD	_ _ _ _	4.1 — 8.4 —	5.0 5.5 10 11	mA

 $\textbf{NOTE:} \quad \textbf{3.} \quad \text{Measured with V}_{\textbf{CC}} \text{ and V}_{\textbf{EE}} \text{ differentially varied simultaneously}.$

AC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics			Min	Тур	Max	Unit
Slew Rate (V_{in} = -10 V to +10 V, R_L = 2.0 k Ω , C_L = 100 pF A_V = +1.	0)	SR	5.0	7.0	_	V/μs
Gain Bandwidth Product (f = 100 kHz)		GBW	10	16	_	MHz
Unity Gain Frequency (Open Loop)		fU	_	9.0	_	MHz
Gain Margin (R _L = 2.0 k Ω)	C _L = 0 pF C _L = 100 pF	A _m	_	-11 -6.0	_	dB
Phase Margin (R _L = $2.0 \text{ k}\Omega$)	C _L = 0 pF C _L = 100 pF	φm	_	55 40	_	Degree s
Channel Separation (f = 20 Hz to 20 kHz)		CS	_	-120	_	dB
Power Bandwidth ($V_O = 27 V_{pp}$, $R_L = 2.0 k\Omega$, THD $\leq 1.0\%$)		вWp	_	120	_	kHz
Distortion (R _L = $2.0 \text{ k}\Omega$, f = 20 Hz to 20 kHz , $V_O = 3.0 \text{ V}_{rms}$, $A_V = +1.0$)			_	0.002	_	%
Open Loop Output Impedance (V _O = 0 V, f = 9.0 MHz)		ZO	_	37	_	Ω
Differential Input Resistance (V _{CM} = 0 V)		R _{IN}	_	175	_	kΩ
Differential Input Capacitance (V _{CM} = 0 V)		C _{IN}	_	12	_	pF
Equivalent Input Noise Voltage (Rs = 100 Ω , f = 1.0 kHz)				4.5		nV/√Hz
Equivalent Input Noise Current (f = 1.0 kHz)		i _n	_	0.5	_	pA/√Hz

Figure 1. Maximum Power Dissipation versus Temperature

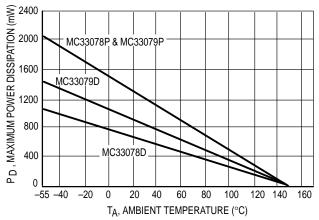


Figure 3. Input Bias Current versus Temperature

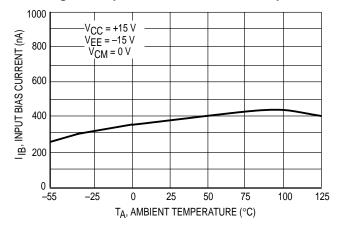


Figure 2. Input Bias Current versus Supply Voltage

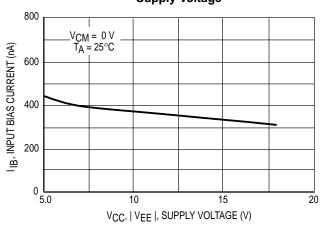


Figure 4. Input Offset Voltage versus Temperature

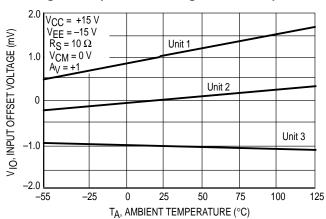


Figure 5. Input Bias Current versus **Common Mode Voltage** 600 V_{CC} = +15 V V_{EE} = -15 V 500 IB, INPUT BIAS CURRENT (nA) T_A = 25°C 400 300 200 100 0 -15 -10 5.0 10 15 -5.0

V_{CM}, COMMON MODE VOLTAGE (V)

Figure 6. Input Common Mode Voltage Range versus Temperature V_{ICR}, INPUT COMMON MODE VOLTAGE RANGE (V) VCC -0 V_{CC} -0.5 +VCM $V_{CC} = +3.0 \text{ V to } +15 \text{ V}$ V_{CC} -1.0 $V_{EE} = -3.0 \text{ V to } -15 \text{ V}$ $\Delta V_{IO} = 5.0 \text{ mV}$ VCC -1.5 $V_0 = 0 V$ Voltage Range VEE +1.5 VEE +1.0 -VCM VEE +0.5 VEE+0 -25 125 -55 25 50 75 100 TA, AMBIENT TEMPERATURE (°C)

Figure 7. Output Saturation Voltage versus Load Resistance to Ground

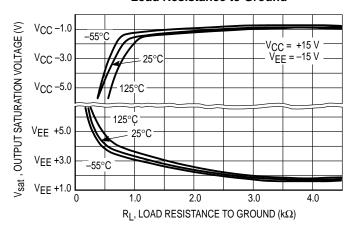


Figure 8. Output Short Circuit Current versus Temperature

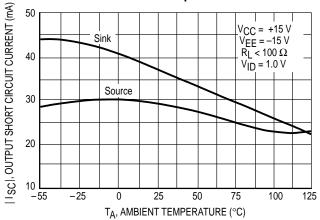


Figure 9. Supply Current versus Temperature

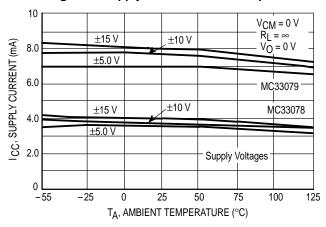


Figure 10. Common Mode Rejection versus Frequency

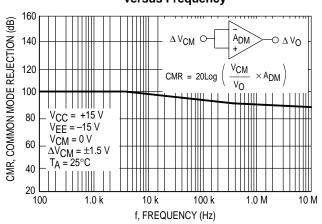


Figure 11. Power Supply Rejection versus Frequency

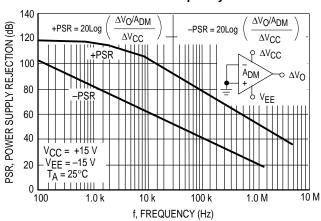


Figure 12. Gain Bandwidth Product versus Supply Voltage

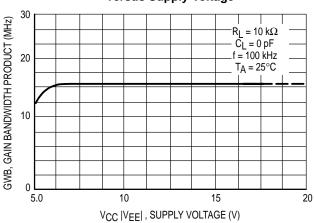


Figure 13. Gain Bandwidth Product versus Temperature

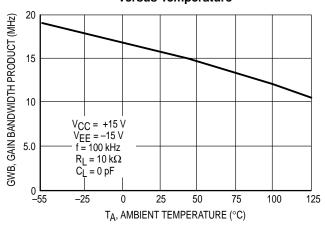


Figure 14. Maximum Output Voltage versus Supply Voltage

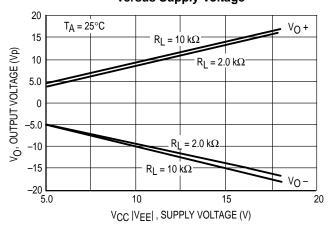


Figure 15. Output Voltage versus Frequency

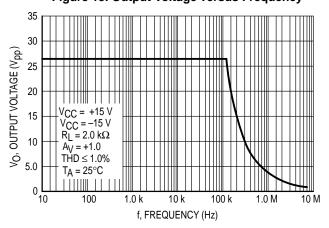


Figure 16. Open Loop Voltage Gain versus Supply Voltage

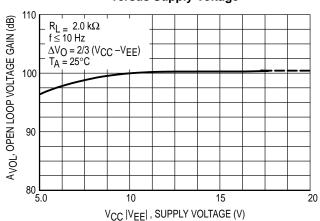


Figure 17. Open Loop Voltage Gain versus Temperature

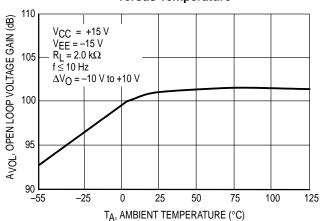


Figure 18. Output Impedance versus Frequency

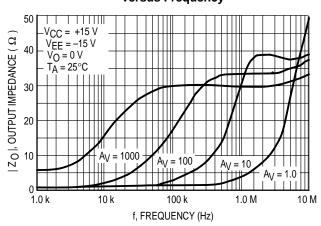


Figure 19. Channel Separation versus Frequency

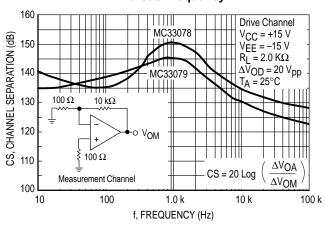


Figure 20. Total Harmonic Distortion versus Frequency

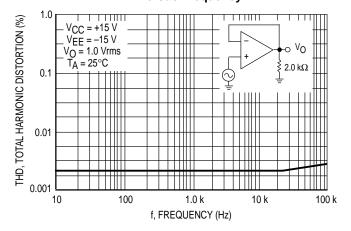


Figure 21. Total Harmonic Distortion versus Output Voltage

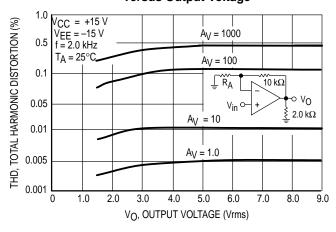


Figure 22. Slew Rate versus Supply Voltage

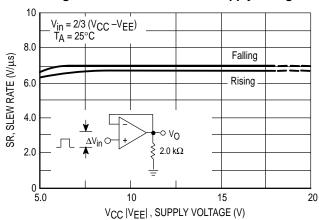


Figure 23. Slew Rate versus Temperature

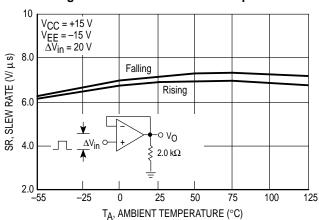


Figure 24. Voltage Gain and Phase versus Frequency

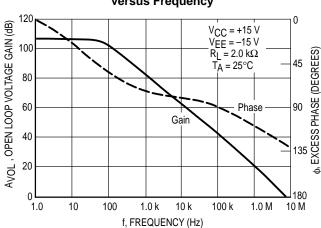


Figure 25. Open Loop Gain Margin and Phase Margin versus Load Capacitance

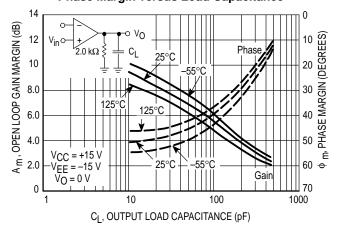


Figure 26. Overshoot versus Output Load Capacitance

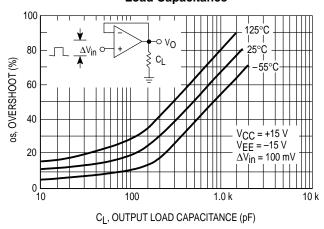


Figure 27. Input Referred Noise Voltage and

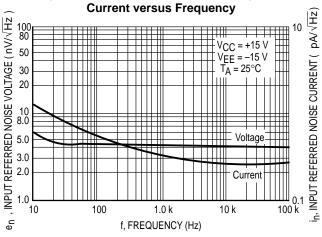


Figure 28. Total Input Referred Noise Voltage versus Source Resistance

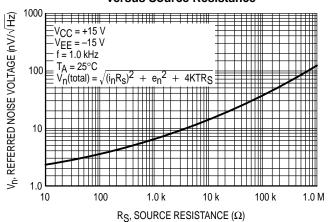


Figure 29. Phase Margin and Gain Margin versus Differential Source Resistance

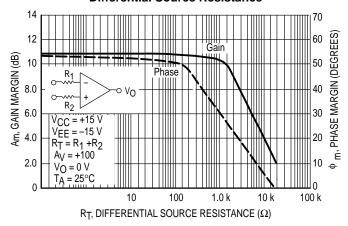


Figure 30. Inverting Amplifier Slew Rate

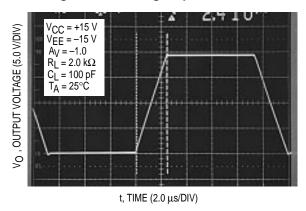


Figure 31. Noninverting Amplifier Slew Rate

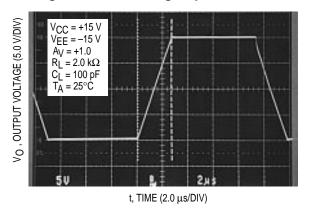


Figure 32. Noninverting Amplifier Overshoot

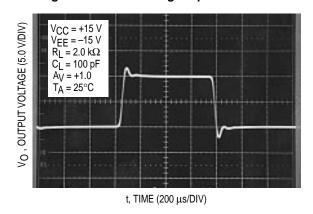


Figure 33. Low Frequency Noise Voltage versus Time

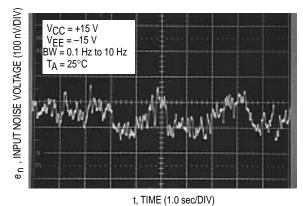
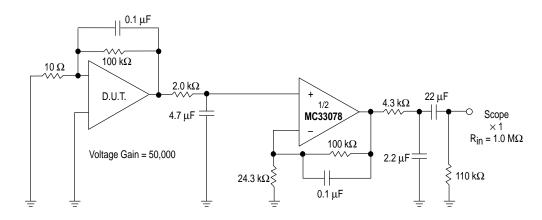
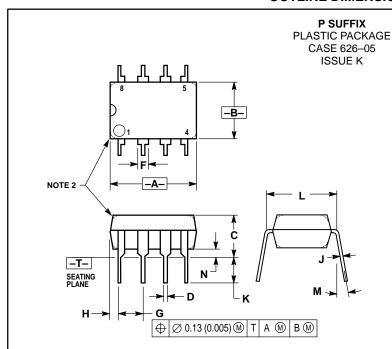


Figure 34. Voltage Noise Test Circuit (0.1 Hz to 10 Hz_{p-p})



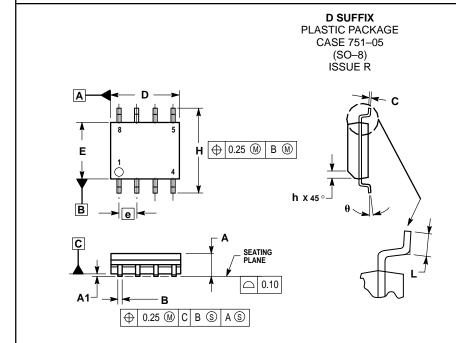
Note: All capacitors are non-polarized.

OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
 3. DIMENSIONING AND TOLERANCING PER ANSI 741 6487 Y14.5M, 1982.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54	BSC	0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300	BSC
М		10°		10°
N	0.76	1.01	0.030	0.040



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. DIMENSIONS ARE IN MILLIMETERS.

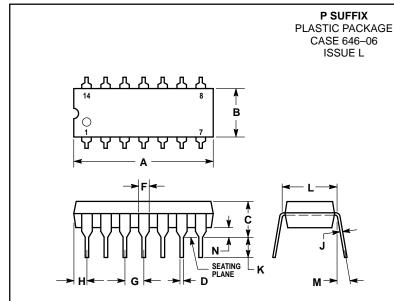
 3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

 5. DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

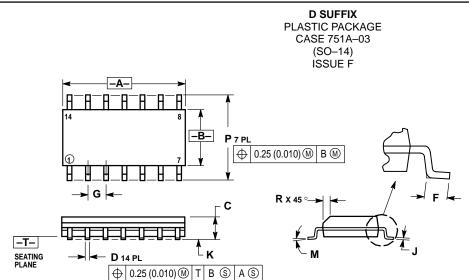
	MILLIMETERS			
DIM	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
В	0.35	0.49		
C	0.18	0.25		
D	4.80	5.00		
Е	3.80	4.00		
е	1.27	BSC		
Η	5.80	6.20		
h	0.25	0.50		
۲	0.40	1.25		
θ	0 °	7 °		

OUTLINE DIMENSIONS



- NOTES: 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
- DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD
- FLASH.
- 4. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.715	0.770	18.16	19.56	
В	0.240	0.260	6.10	6.60	
С	0.145	0.185	3.69	4.69	
D	0.015	0.021	0.38	0.53	
F	0.040	0.070	1.02	1.78	
G	0.100 BSC		2.54 BSC		
Н	0.052	0.095	1.32	2.41	
J	0.008	0.015	0.20	0.38	
K	0.115	0.135	2.92	3.43	
L	0.300 BSC		7.62	BSC	
М	0°	10°	0°	10°	
N	0.015	0.039	0.39	1.01	



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

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